■ General Description

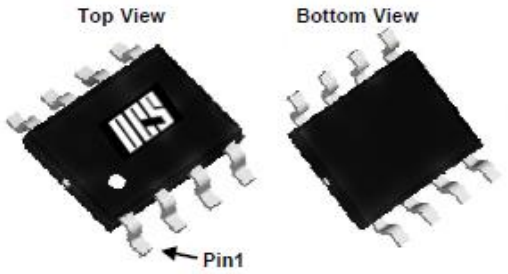
The OCM4611Suses advanced trench technology to provide excellent RDS(ON)and low gate charge .The complementary MOSFET may be used to form a level shifted high side switch, and for a host of other applications.

■ General Features

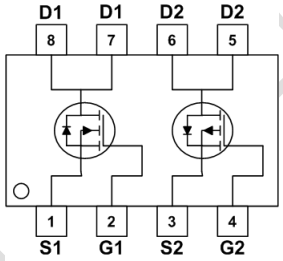
N-Channel	P-Channel
V_{DS}= 60V,I_D=7A	V_{DS}= -60V,I_D=-5.5A
$R_{DS(ON)}$<32m Ω@ V_{GS}=10V	$R_{DS(ON)}$<60m Ω@ V_{GS}=-10V
$R_{DS(ON)}$<45m Ω@ V_{GS}=4.5V	$R_{DS(ON)}$<75m Ω@ V_{GS}=-4.5V

■ Application

- High power and current handing capability
- BLDC
- Others application



Marking and Pin assignment



Schematic diagram

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter		Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage		V_{DS}	60	-60	V
Gate-Source Voltage		V_{GS}	±20	±20	V
Continuous Drain Current	T_A=25℃	I_D	7	-5.5	A
	T_A=70℃		5.5	-4.5	
Pulsed Drain Current (Note 2)		I_{DM}	46	-40	A
Single Pulse Avalanche(Note 3)		EAS	25.5	35.5	mJ
Avalanche Current		I_{AS}	22.6	-26.6	A
Maximum Power Dissipation(Note4)	T_A=25℃	PD	1.5	1.5	W
Operating Junction and Storage Temperature Range		T_J,T_{STG}	-55 To 150	-55 To 150	℃

Thermal Characteristic

Parameter	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient(Note 1)	$R_{\theta JA}$	85	℃/W
Thermal Resistance, Junction-to-Case(Note 1)	$R_{\theta JC}$	36	℃/W

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